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SEMICONDUCTOR

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74F219 64-Bit Random Access Memory with 3-STATE Outputs

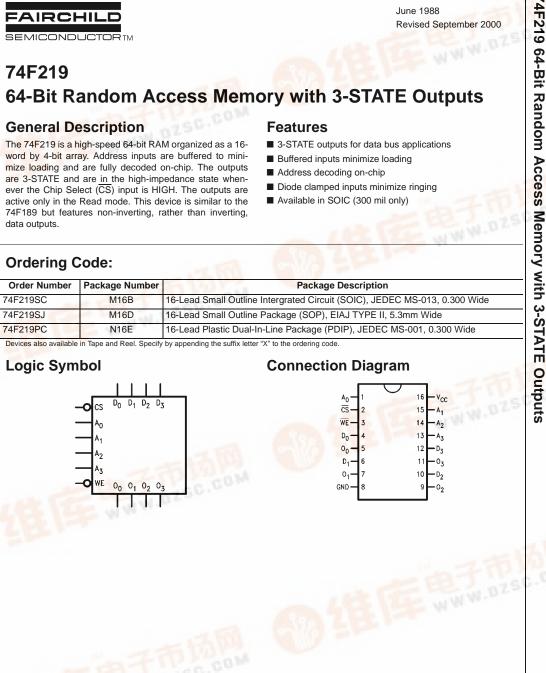
General Description

The 74F219 is a high-speed 64-bit RAM organized as a 16word by 4-bit array. Address inputs are buffered to mini-mize loading and are fully decoded on-chip. The outputs are 3-STATE and are in the high-impedance state whenever the Chip Select (CS) input is HIGH. The outputs are active only in the Read mode. This device is similar to the 74F189 but features non-inverting, rather than inverting, data outputs.

- **Features**
- 3-STATE outputs for data bus applications
- Buffered inputs minimize loading
- Address decoding on-chip
- Diode clamped inputs minimize ringing
- Available in SOIC (300 mil only)

Ordering Code:

Order Number	Package Number	Package Description
74F219SC	M16B	16-Lead Small Outline Intergrated Circuit (SOIC), JEDEC MS-013, 0.300 Wide
74F219SJ	M16D	16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74F219PC	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide
Devices also available	in Tape and Reel. Specify	by appending the suffix letter "X" to the ordering code.





74F219

Unit Loading/Fan Out

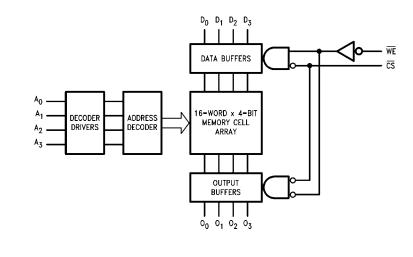
Din Manua	Description	U.L.	Input I _{IH} /I _{IL}		
Pin Names	Description	HIGH/LOW Output I _{OH} /I _{OL} 1.0/1.0 20 μA/-0.6 mA 1.0/2.0 20 μA/-1.2 mA 1.0/1.0 20 μA/-0.6 mA 1.0/1.0 20 μA/-0.6 mA	Output I _{OH} /I _{OL}		
$\frac{A_0 - A_3}{\overline{CS}}$	Address Inputs	1.0/1.0	20 µA/–0.6 mA		
CS	Chip Select Input (Active LOW)	1.0/2.0	20 μA/–1.2 mA		
WE	Write Enable Input (Active LOW)	1.0/1.0	20 µA/–0.6 mA		
D ₀ D ₃	Data Inputs	1.0/1.0	20 µA/–0.6 mA		
D ₀ –D ₃ O ₀ –O ₃	3-STATE Data Outputs	150/40 (33.3)	-3 mA/24 mA (20 mA)		

Function Table

	Inputs		Operation	Condition of Outputs			
ĺ	CS	WE	Operation	Condition of Outputs			
ĺ	L	L	Write	High Impedance			
	L	н	Read	True Stored Data			
	н	х	Inhibit	High Impedance			
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H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial

Block Diagram



Absolute Maximum Ratings(Note 1)

Storage Temperature	$-65^{\circ}C$ to $+150^{\circ}C$
Ambient Temperature under Bias	$-55^{\circ}C$ to $+125^{\circ}C$
Junction Temperature under Bias	$-55^{\circ}C$ to $+150^{\circ}C$
V _{CC} Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Output	
in HIGH State (with $V_{CC} = 0V$)	
Standard Output	-0.5V to V _{CC}
3-STATE Output	-0.5V to +5.5V
Current Applied to Output	
in LOW State (Max)	twice the rated I_{OL} (mA)

Recommended Operating Conditions

Free Air Ambient Temperature	
Supply Voltage	

74F219

 $0^{\circ}C$ to $+70^{\circ}C$

+4.5V to +5.5V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol	Parameter		Min	Тур	Max	Units	Vcc	Conditions
VIH	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal
V _{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal
V _{CD}	Input Clamp Diode Voltage				-1.2	V	Min	I _{IN} = -18 mA
V _{OH}	Output HIGH	10% V _{CC}	2.5					I _{OH} = -1 mA
	Voltage	10% V _{CC}	2.4			v	Min	$I_{OH} = -3 \text{ mA}$
		5% V _{CC}	2.7			v	IVIIII	$I_{OH} = -1 \text{ mA}$
		5% V _{CC}	2.7					$I_{OH} = -3 \text{ mA}$
V _{OL}	Output LOW	10% V _{CC}			0.5	V	Min	I _{OL} = 24 mA
	Voltage							
I _{IH}	Input HIGH				5.0	۸	Max	V _{IN} = 2.7V
	Current				5.0	μA	IVIAX	$v_{\rm IN} = 2.7 v$
I _{BVI}	Input HIGH Current				7.0	μA	Max	V _{IN} = 7.0V
	Breakdown Test				7.0	μΛ	IVIAA	v _{IN} = 7.0 v
I _{CEX}	Output HIGH				50	μA	Max	V _{OUT} = V _{CC}
	Leakage Current				50	μΛ	IVIAA	VOUT - VCC
V _{ID}	Input Leakage		4.75			V	0.0	I _{ID} = 1.9 μA
	Test		4.75			v	0.0	All Other Pins Grounded
I _{OD}	Output Leakage				3.75	μΑ 0.0	0.0	V _{IOD} = 150 mV
	Circuit Current				5.75	μΛ	0.0	All Other Pins Grounded
կլ	Input LOW				-0.6			$V_{IN} = 0.5V (A_n, \overline{WE}, D_n)$
	Current				-1.2	mA	Max	$V_{IN} = 0.5V \ (\overline{CS})$
I _{OZH}	Output Leakage Current				50	μΑ	Max	V _{OUT} = 2.7V
I _{OZL}	Output Leakage Current				-50	μA	Max	V _{OUT} = 0.5V
I _{OS}	Output Short-Circuit Current		-60		-150	mA	Max	$V_{OUT} = 0V$
I _{ZZ}	Bus Drainage Test				500	μA	0.0V	V _{OUT} = 5.25V
I _{CC}	Power Supply Current			37	55	mA	Max	

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AC Electrical Characteristics

Symbol	Parameter	$T_{A} = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$			$T_{A} = -55^{\circ}C \text{ to } +125^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$		T _A = 0°C to +70°C V _{CC} = +5.0V C ₁ = 50 pF		Units
		Min	Тур	Max	Min	Max	Min	Max	
t _{PLH}	Access Time, HIGH or LOW	10.0	18.5	26.0	9.0	32.0	10.0	27.0	
t _{PHL}	A _n to O _n	8.0	13.5	19.0	8.0	23.0	8.0	20.0	ns
t _{PZH}	Access Time, HIGH or LOW	3.5	6.0	8.5	3.5	10.5	3.5	9.5	
t _{PZL}	CS to O _n	5.0	9.0	13.0	5.0	15.0	5.0	14.0	
t _{PHZ}	Disable Time, HIGH or LOW	2.0	4.0	6.0	2.0	8.0	2.0	7.0	ns
t _{PLZ}	CS to O _n	3.0	5.5	8.0	2.5	10.0	3.0	9.0	
t _{PZH}	Write Recovery Time	6.5	20.0	28.0	6.5	37.5	6.5	29.0	
t _{PZL}	HIGH or LOW, WE to On	6.5	11.0	15.5	6.5	17.5	6.5	16.5	
t _{PHZ}	Disable Time, HIGH or LOW	4.0	7.0	10.0	3.5	12.0	4.0	11.0	ns
t _{PLZ}	WE to On	5.0	9.0	13.0	5.0	15.0	5.0	14.0	

AC Operating Requirements

		$T_A = +25^{\circ}C$		$T_A = -55^{\circ}C$ to $+125^{\circ}C$		$T_A = 0^{\circ}C \text{ to } +70^{\circ}C$		
Symbol	Parameter	V _{CC} =	$V_{CC} = +5.0V$		$V_{CC} = +5.0V$		$V_{CC} = +5.0V$	
		Min	Max	Min	Max	Min	Max	
t _S (H)	Setup Time, HIGH or LOW	0		0		0		
t _S (L)	A _n to WE	0		0		0		ns
t _H (H)	Hold Time, HIGH or LOW	2.0		2.0		2.0		115
t _H (L)	A _n to WE	2.0		2.0		2.0		
t _S (H)	Setup Time, HIGH or LOW	10.0		11.0		10.0		
t _S (L)	D _n to WE	10.0		11.0		10.0		ns
t _H (H)	Hold Time, HIGH or LOW	0		2.0		0		115
t _H (L)	D _n to WE	0		2.0		0		
t _S (L)	Setup Time, LOW CS to WE	0		0		0		ns
t _H (L)	Hold Time, LOW CS to WE	6.0		7.5		6.0		115
t _W (L)	WE Pulse Width, LOW	6.0		15.0		6.0		ns

